



SPIN-FILTERED PHOTOEMISSION AND POLARIMETRY EFFORTS AT EUCLID

ERIC MONTGOMERY

EUCLID TECHLABS / EUCLID BEAMLABS

P3 WORKSHOP - NOVEMBER 2021



Team

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We gratefully acknowledge primary funding of this work by the U.S. Department of Energy Office of Nuclear Physics under SBIR grants DE-SC0021509 and DE-SC0020564. Additional funding for UNI and SD State was by National Science Foundation (NSF) Grants 2003828 and 2003856.



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Outline

1. Half Metal Spin Filters

GaAs Spin Polarized Photocathodes

State of the Art

Proposal: Half metals on GaAs

2. DFT Studies

Crystal & Electronic Structure of CrMnSb

Mechanical strain

Sb -> P substitution

Biaxial strain in thin films of CrMnSb_{0.5}P_{0.5}

DFT Conclusions

3. Half Heusler QE Experiments

Deposition and Transport

Preliminary data

4. Side Topic: Diamond Polarimetry

Motivation

Apparatus

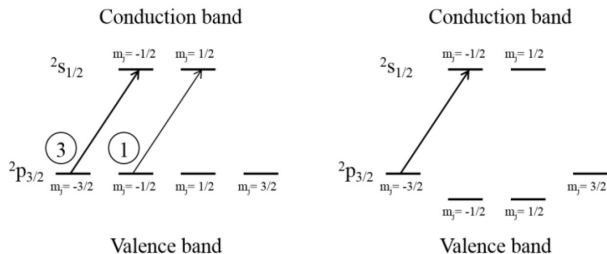
Initial CEBAF data

GaAs Spin-Polarized Photoemission

GaAs chosen because it forms a negative electron affinity surface (for high quantum efficiency). Spin polarized emission is possible from bulk (typ. ~30%, theory 50%), on the left. Axial strain, on the right, breaks degeneracy and improves spin polarization (typ. ~80%, theory 100%).

Other methods such as multi-photon emission and OAM light have yielded poor results.¹

¹McCarter et al., "Novel Approaches for Electron Beam Polarization", Proc. PSTP (2013).



State of the Art Spin-Polarized Photocathodes

Distributed Bragg reflector strained superlattice GaAs/GaAsP photocathode with Cs-F negative electron affinity activation layer, used at CEBAF (JLab):

- QE 6%¹,
- polarization 84%¹

¹Liu et al., Appl. Phys. Lett 109, 252104, 2016.

Standard strained superlattice GaAs/GaAsP with Cs-F³:

- QE up to 1.6%²,
- polarization up to 92%²

²Jin et al., Appl. Phys. Lett. 105, 203509, 2014

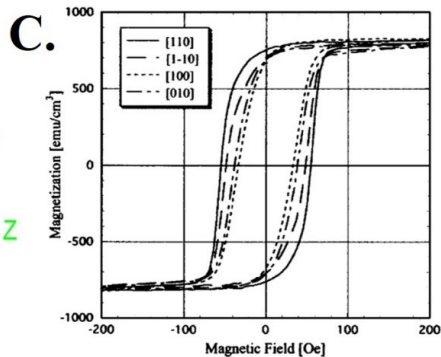
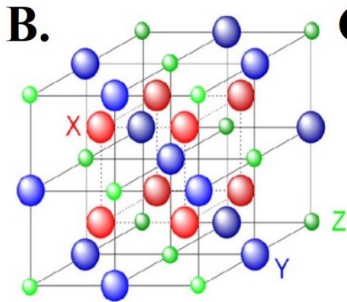
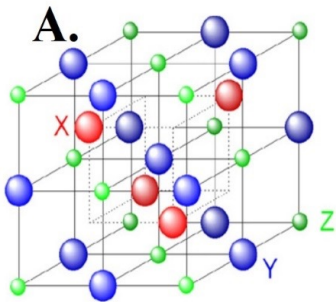
³Maruyama et al., Appl. Phys. Lett. 85, 2640, 2004.

GaAs	5 nm	$p=5 \times 10^{19} \text{ cm}^{-3}$
GaAs/GaAsP SL	(3.8/2.8 nm) $\times 14$	$p=5 \cdot 10^{17} \text{ cm}^{-3}$
GaAsP _{0.35}	750 nm	$p=5 \times 10^{18} \text{ cm}^{-3}$
GaAsP _{0.35} /AlAsP _{0.4} DBR	(54/64 nm) $\times 12$	$p=5 \times 10^{18} \text{ cm}^{-3}$
GaAsP _{0.35}	2000 nm	$p=5 \times 10^{18} \text{ cm}^{-3}$
Graded GaAsP _x (x = 0-0.35)	5000 nm	$p=5 \times 10^{18} \text{ cm}^{-3}$
GaAs buffer	200 nm	$p=2 \times 10^{18} \text{ cm}^{-3}$
p-GaAs substrate ($p > 10^{18} \text{ cm}^{-3}$)		

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GaAs/GaAsP SL	(3.8/2.8 nm) $\times 14$	$p=5 \times 10^{17} \text{ cm}^{-3}$
GaAsP _{0.35}	2750 nm	$p=5 \times 10^{18} \text{ cm}^{-3}$
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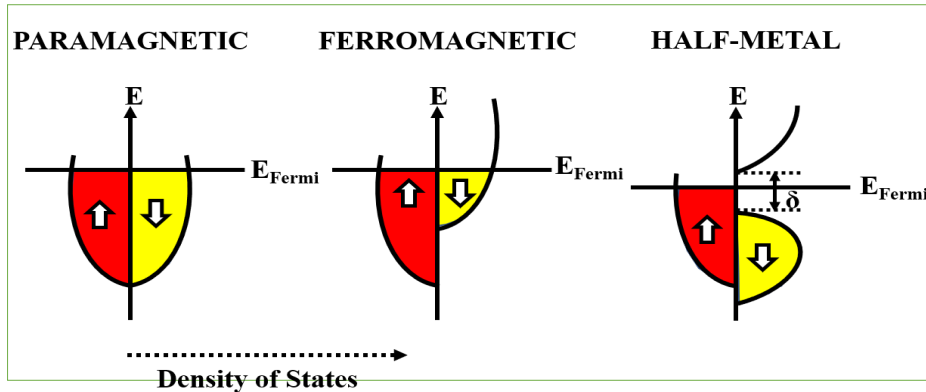
Heusler Alloys

- **Intermetallic: XYZ or X₂YZ**
- **X, Y are transition metals; Z is p-band element**
- **High Curie T (1100 °C) ferromagnet**
- **Lattice matched with III-V semiconductors**
- **Transition metals - multiple oxidation states; prone to oxidation**
- **Require controlled environment (U/XHV)**



Half-Metallicity

- Common metals like copper (Cu) or aluminum (Al) have no net P : half the electrons are \uparrow and half are \downarrow at the Fermi Level (E_F).
- Ferromagnets, e.g., iron (Fe) and cobalt (Co) have small imbalance of \uparrow and \downarrow electrons at E_F .
- Half-metals (HM) the majority spin channel is metallic while the minority channel is insulating (See Fig. below).
- The majority spin band (denoted by upwards arrow) has no band gap at E_F while the minority band possess a finite band gap δ .
- Can result in a population of filled conduction band states with 100 % spin polarization.



Proposal: Half metal spin filters

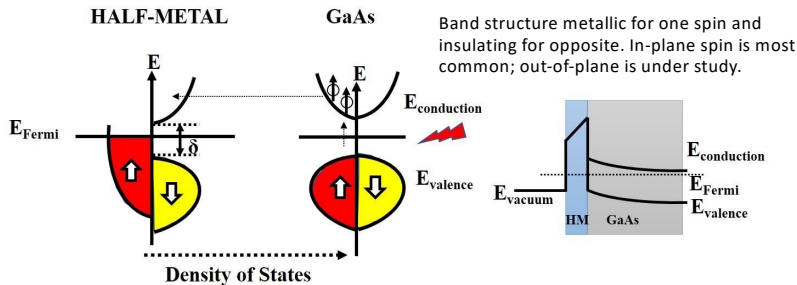
Half metals, discovered in the early 1980s, are untested filters for spin polarized photoemission

We focused on the “Half Heusler” family

Benefits: III-V lattice match, up to 100% spin polarization in bulk, low coercivity

DFT search for new spin filter candidates yielded $\text{CrMnSb}_{0.5}\text{P}_{0.5}$ (JAP, 2020, below), other non-phosphorus options under study

Intro first, then a bit of DFT...



Chemical substitution induced half-metallicity in $\text{CrMnSb}_{(1-x)}\text{P}_x$

Cite as: J. Appl. Phys. **128**, 113906 (2020); doi: [10.1063/5.0021467](https://doi.org/10.1063/5.0021467)

Submitted: 10 July 2020 · Accepted: 23 August 2020 ·

Published Online: 21 September 2020



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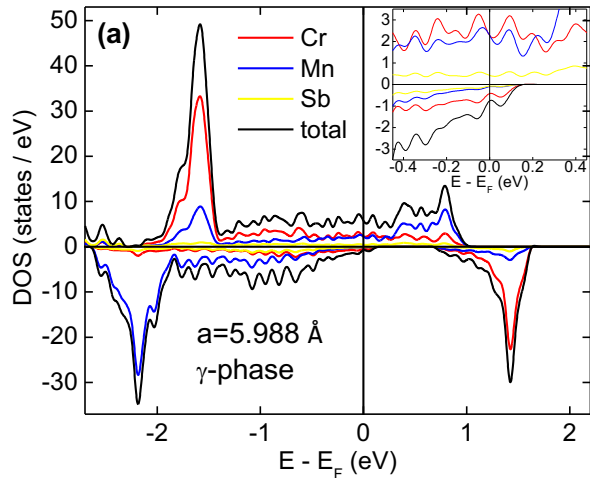
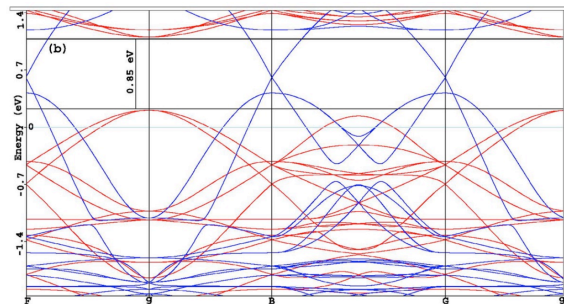
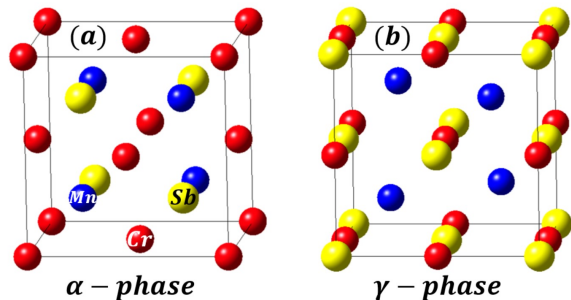
Evan O’Leary,¹ Adam Ramker,¹ Devon VanBrogen,¹ Bishnu Dahal,² Eric J. Montgomery,³ Shashi Poddar,³ Parashu Kharel,² Andrew J. Stollenwerk,¹ and Pavel V. Lukashev^{1,a)}

DFT Studies

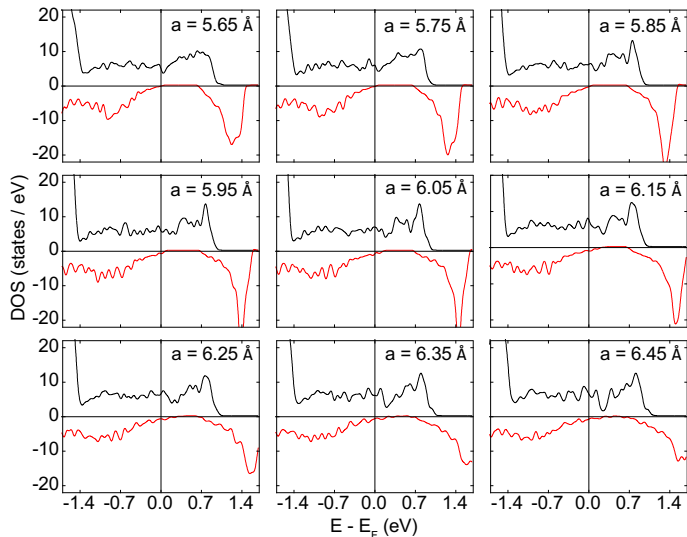
- Software:
 - Density Functional calculations
 - Vienna *Ab-Initio* Simulation package (VASP)
- Hardware:
 - Local: UNI Physics computer cluster
 - External: Pittsburgh Supercomputing Center – Bridges



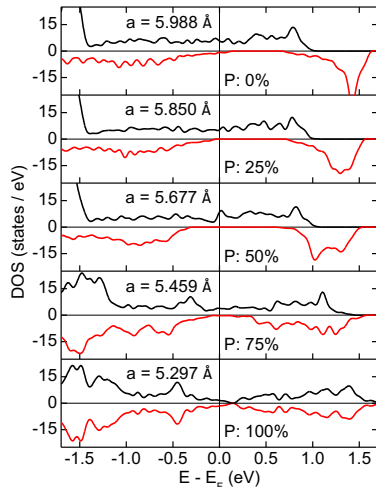
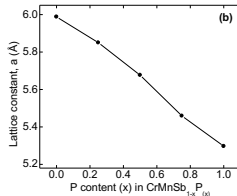
CrMnSb crystal and electronic structure



CrMnSb and P substitution



biaxial strain

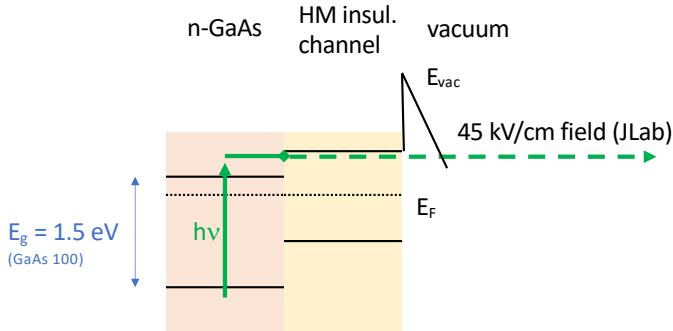


DFT Summary

- **CrMnSb: *nearly* half-metallic electronic structure in ground state.**
- **Half-metallic transition under uniform pressure.**
- **Biaxial strain (thin film) – no HM transition.**
- **Chemical substitution induced half-metallicity: Sb → P.**
- **CrMnSb_{0.5}P_{0.5} – a new proposed material which is a fully compensated half-metallic ferrimagnet suitable for spin filtering.**
- **Complementary to known fully compensated half-metallic ferrimagnets, such as the full Heusler alloys Co₂FeSi and Co₂MnSi.**

Half metal spin filter band diagram

Band diagram suggests half metal growth on heavily doped n-type GaAs.



Vacuum emission for one spin state possible with NEA condition and/or tunneling through field-lowered barrier

- A large Slater-Pauling gap (Δ) in the half metal and a low emission barrier are desirable
- Cesium and high field will be required for good QE

Half metal spin filter “wish list”

High emitted spin polarization if...

1. 100% polarized at E_F
2. P-type substrate doped so conduction band below that of half metal minority channel
3. Properly terminated
4. Lattice matched so low disorder

High quantum efficiency if...

1. Large minority band gap
2. Cs-F compatible (no alloying @r.t.)
3. Thin half metal – 1-3 formula units

(optional) practically, easier to use if...

1. High Curie temperature
2. Moderate magnetic coercivity
3. Fully compensated magnetic moment so no intrinsic angular momentum of photoemitted electrons (otherwise may need a bucking coil)

Half metal spin filter selection

Co₂FeSi and Co₂MnSi selected

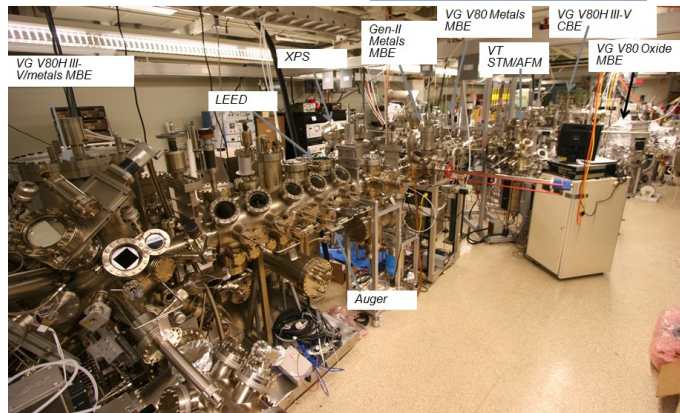
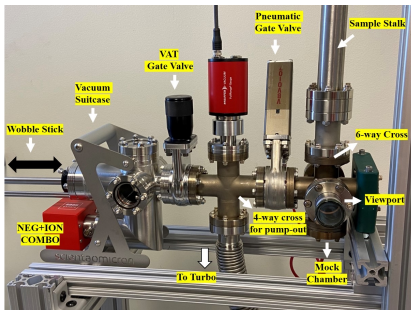
- Ease of growth
- close lattice matching with GaAs
- highest magnetic moments.

Univ. of California-Santa Barbara (Palmstrøm Lab) grew both on heavily n-doped GaAs.

Heusler Alloy	Curie Temperature (Kelvin)	Magnetic Moment ($\mu\text{B}/\text{formula unit}$)	Lattice mismatch with GaAs (%)
Co ₂ FeSi	1100	5.46	0.08
Co ₂ FeAl	1000	4.98	1.3
Co ₂ MnSi	985	5.0	0.3
Co ₂ MnGe	905	5.0	1.6
Co ₂ MnAl	726	4.0	1.8

5 nm Co ₂ MnSi/Co ₂ FeSi
2 μm nGaAs (Si: $5 \times 10^{18} \text{ cm}^{-3}$)
500 nm UID GaAs
SI GaAs (AXT)

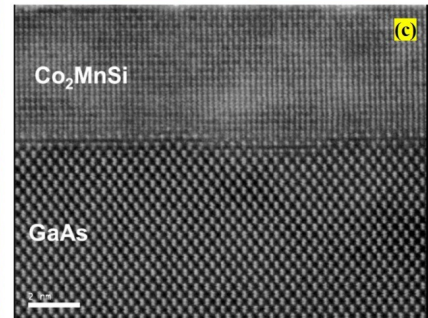
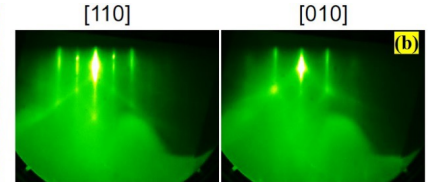
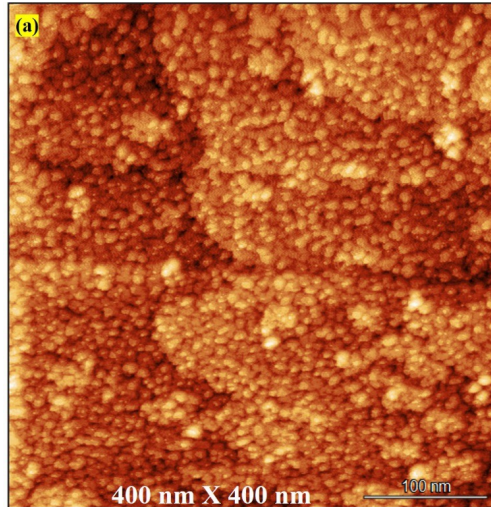
Transfer to JLab at 10^{-11} Torr via custom Omicron vacuum suitcase to cesiate, measure QE and attempt Mott polarimetry



Characterization after growth at UCSB

- (a) STM surface scan (scale 100 nm)
- (b) RHEED pattern
- (c) HAADF-TEM scan for the Co_2MnSi on GaAs system (scale 2 nm)

High angle annular dark-field (HAADF) detects Rutherford-scattered electrons as opposed to Bragg-scattered: dark-field contrast improves for higher Z. HAADF-TEM is uniquely suited for imaging of strain relaxation in cross-sections of epitaxial interfaces.



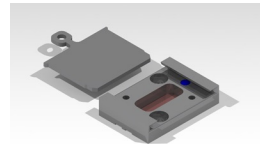
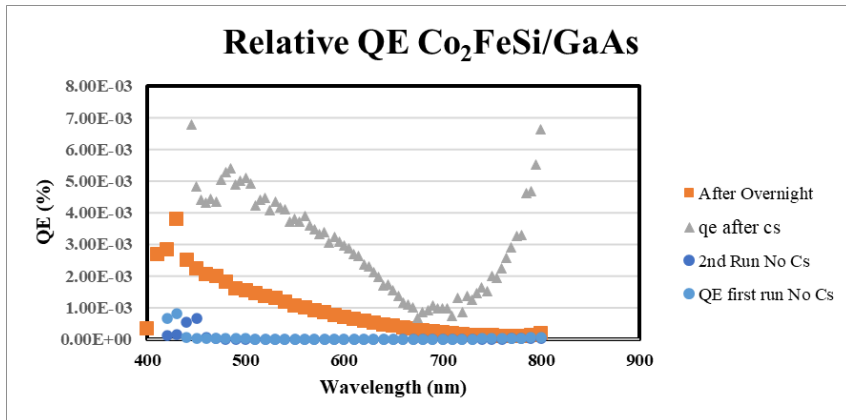
Cesiation and Quantum Efficiency

Transfer in UHV suitcase from UCSB to JLab's modified polarimeter for flag-style Omicron samples was successful. (!!)

Heat clean and Cs/NF₃ yo-yo immediately produced photocurrent, suggesting Cs-F submonolayer adsorption as desired, the Cs not alloying with the bulk.

QE in the visible (gray curve) is an order of magnitude reduced from GaAs. Assessment of spin filtering requires polarimetry (next!)

Lifetime in the polarimeter is a few hours to 1/e - the QE falls overnight (orange curve). Residual NF₃ is a possible suspect.



Mott Polarimetry

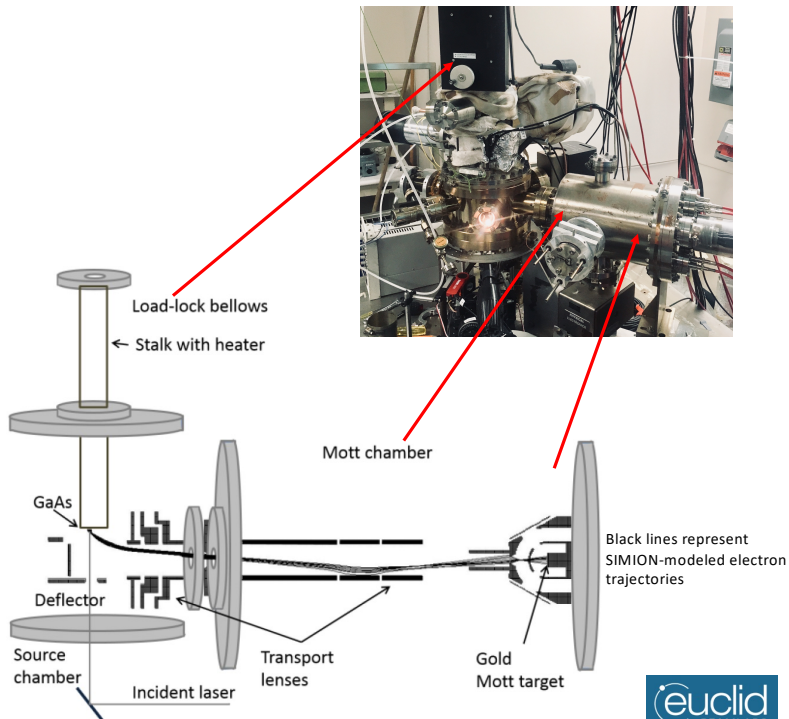
Mott polarimetry exploits elastic scattering asymmetry of spin polarized electrons from nuclear Coulomb field.

$$\sigma(\theta) = I(\theta) [1 + S(\theta) \mathbf{P} \cdot \mathbf{n}]$$

$$P = \frac{N_{\uparrow} - N_{\downarrow}}{N_{\uparrow} + N_{\downarrow}}$$

Requires known Sherman function S

Illumination is with circularly polarized light



Polarimetry – $\text{Co}_2\text{FeSi}/\text{GaAs}$

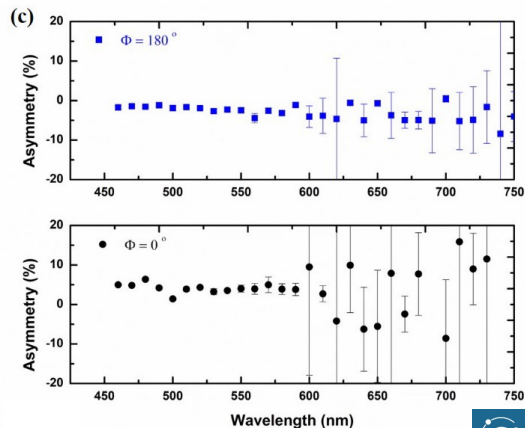
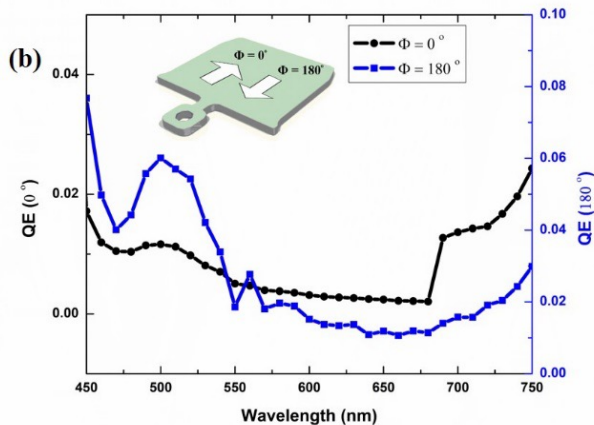
Linearly polarized normally incident illumination.

(b) Average QE after in-plane magnetic poling at 0 and 180.

(c) Total asymmetry* via Mott polarimetry for the two cases.

Asymmetry switches sign, indicating spin-filtering. Estimated polarization could be ~60-70% though statistics were not ideal due to time limitations*.

Unclear why spin filtering persists with excess photon energy greater than the half-metal minority spin channel band gap ~0.5 eV.



*Very challenging experiment. Not repeated; systematic errors possible.

Polarimetry – $\text{Co}_2\text{MnSi}/\text{GaAs}$

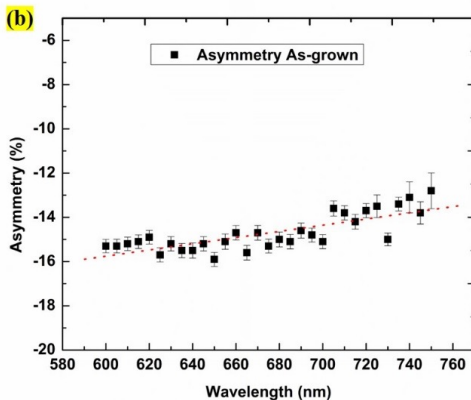
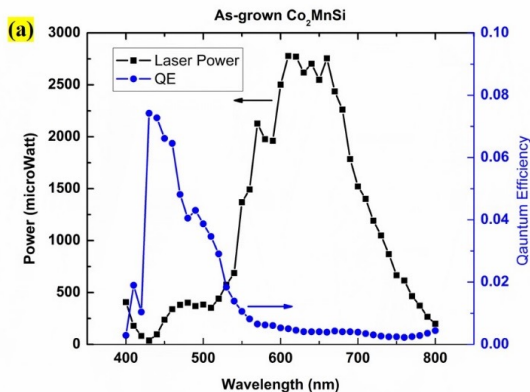
Linearly polarized normally incident illumination.

Only one poled in-plane field direction tested.

Similar QE (blue curve), 10x lower than NEA GaAs.

Asymmetry magnitude may be much higher than for Co_2FeSi^* .

Inconclusive; Covid restrictions and experimental issues precluded a field flip to check sign change of asymmetry.

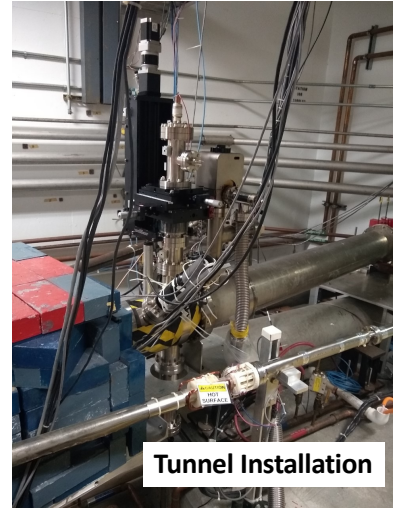


*Very challenging experiment. Not repeated; systematic errors possible.

Half Metal Spin Filter Conclusions

- Two half-Heusler half metals were grown on heavily n-doped GaAs: Co_2FeSi and Co_2MnSi .
- Cesium appears not to alloy with the spin filter.
- Both cesiated half-metals on GaAs photoemit. $\sim 10\times$ QE reduction vs bulk NEA GaAs.
- Note: normally-incident, linearly polarized illumination cannot produce spin polarized emission in GaAs without the action of the spin filter, so any asymmetry beyond experimental uncertainty is a sign of spin filtering.
- It works! Spin polarization suggested by asymmetry which flips with magnetic poling direction.
- Quantification of polarization was not possible; rough estimates of 60-70% leave much room for improvement towards the theoretical 100%.
- Near-XHV conditions during handling were not easy; a more stable filter would be preferable.
- In-plane polarization is not ideal; out-of-plane is preferred for longitudinal spin and ease of poling with a solenoid.
- We are continuing to investigate other options for out-of-plane spin filtering with proposals pending. Stay tuned!

Diamond polarimetry – bonus topic!



Diamond polarimetry

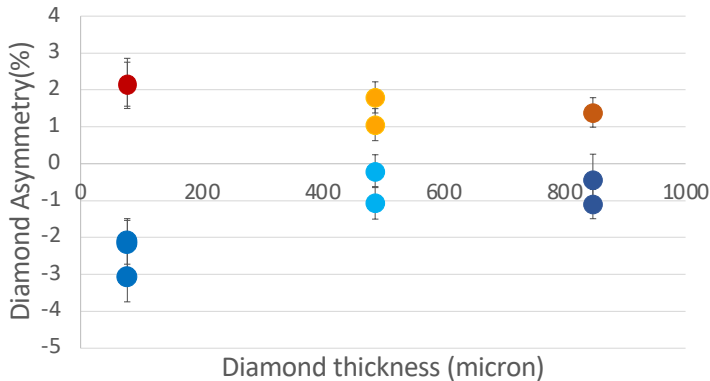
Three CEBAF runs!



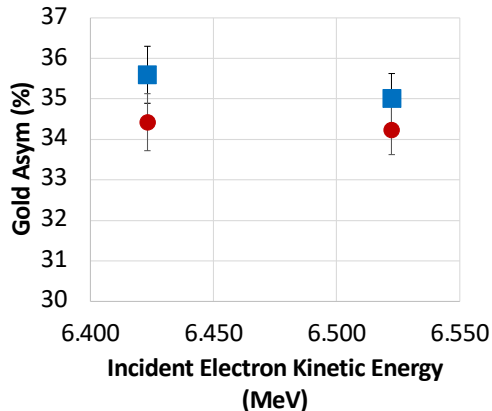
	Energy	Targets
Aug 3 8:00-14:30	6.3 MeV Pockles cell off	Open poly 77 μm 487 μm
Aug 5 15:30-19:00	6.3 MeV	Gold 77 μm 487 μm 847 μm Heating test
Aug 13 8:00-16:00	6.3 MeV	Gold 77 μm , steering 487 μm 847 μm
	4 MeV	77 μm 487 μm 847 μm
	4.5 MeV	77 μm
	5 MeV	77 μm

6.3 MeV asymmetry - Diamond vs Gold

Could replace gold as Mott target for high current beams and high precision foils



- 77 micron OUT
- 77 micron IN
- 487 micron OUT
- 487 micron IN
- 847 micron OUT
- 847 Micron IN



- Gold IHWP_out
- -1*Gold IHWP_IN

Trend toward decreased asymmetry with thickness; minimal heating

Thank you to all P3 attendees
and our organizing committee!